

Features

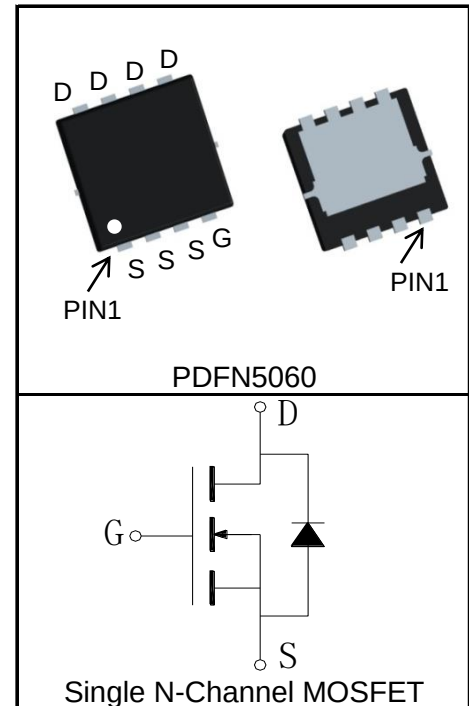
- 40V/55A,
 $R_{DS(ON)} = 7m\Omega(Typ.)@V_{GS}=10V$
 $R_{DS(ON)} = 11m\Omega(Typ.)@V_{GS}=4.5V$
- Low $R_{DS(ON)}$
- Super High Dense Cell Design
- Fast Switching Speed
- 100% avalanche tested

Applications

- Switching Application Systems



Pin Description



Absolute Maximum Ratings

Symbol	Parameter		Rating	Unit
Common Ratings (T _C =25°C Unless Otherwise Noted)				
V _{DSS}	Drain-Source Voltage		40	V
V _{GSS}	Gate-Source Voltage		±20	
T _J	Maximum Junction Temperature		150	°C
T _{STG}	Storage Temperature Range		-55 to 150	°C
I _S	Diode Continuous Forward Current	T _C =25°C	55	A
Mounted on Large Heat Sink				
I _{DP} ^①	300μs Pulse Drain Current Tested	T _C =25°C	220	A
I _D ^②	Continuous Drain Current@T _C (V _{GS} =10V)	T _C =25°C	55	A
		T _C =100°C	34	
	Continuous Drain Current@T _A (V _{GS} =10V) ^③	T _A =25°C	15	
		T _A =70°C	12	
P _D	Maximum Power Dissipation@T _C	T _C =25°C	38	W
		T _C =100°C	15	
	Maximum Power Dissipation@T _A ^③	T _A =25°C	4.2	
		T _A =70°C	2.7	

Symbol	Parameter	Rating	Unit
$R_{\theta JC}$	Thermal Resistance-Junction to Case	3.3	°C/W
$R_{\theta JA}^{③}$	Thermal Resistance-Junction to Ambient	30	°C/W
Drain-Source Avalanche Ratings			
$E_{AS}^{④}$	Avalanche Energy, Single Pulsed	36	mJ

Electrical Characteristics ($T_C=25^{\circ}\text{C}$ Unless Otherwise Noted)

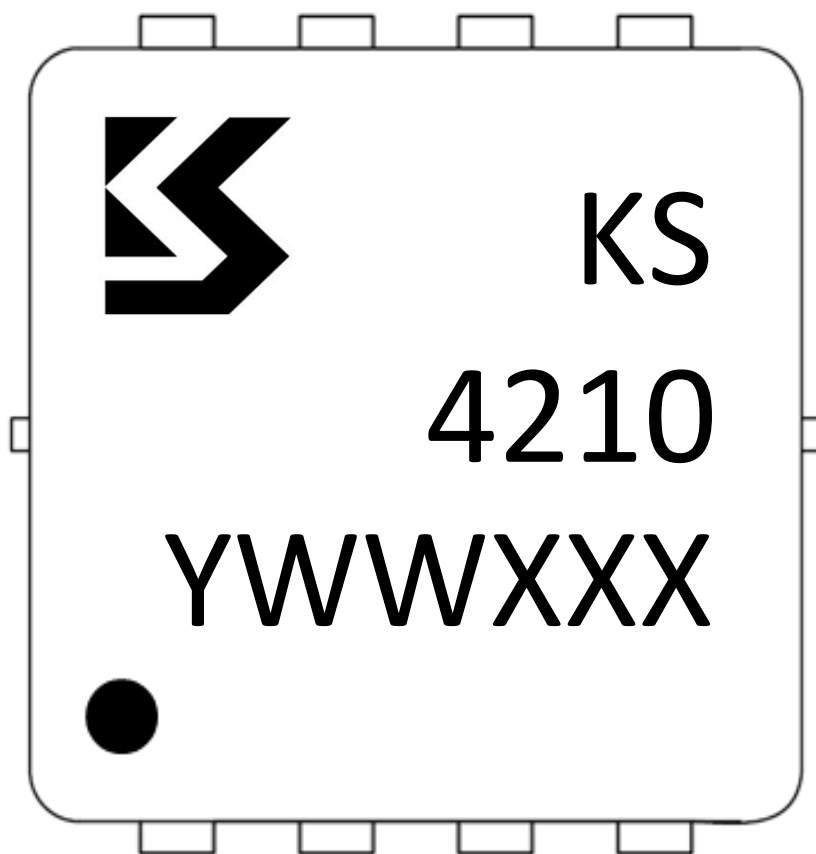
Symbol	Parameter	Test Condition	KS4210NA			Unit
			Min.	Typ.	Max.	
Static Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _{DS} =250μA	40			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =40V, V _{GS} =0V			1	μA
		T _J =125°C			30	
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _{DS} =250μA	1.1	1.5	2.3	V
I _{GSS}	Gate Leakage Current	V _{GS} =±20V, V _{DS} =0V			±100	nA
R _{DS(ON)} ^⑤	Drain-Source On-state Resistance	V _{GS} =10V, I _{DS} =20A		7	10	mΩ
		V _{GS} =4.5V, I _{DS} =15A		11	16	mΩ
Diode Characteristics						
V _{SD} ^⑤	Diode Forward Voltage	I _{SD} =20A, V _{GS} =0V		0.8	1.2	V
t _{rr}	Reverse Recovery Time	I _{SD} =20A, dI _{SD} /dt=100A/μs		14		ns
Q _{rr}	Reverse Recovery Charge			51		nC
Dynamic Characteristics ^⑥						
R _G	Gate Resistance	V _{GS} =0V, V _{DS} =0V, F=1MHz		0.6		Ω
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =20V, Frequency=1.0MHz		2155		pF
C _{oss}	Output Capacitance			160		
C _{rss}	Reverse Transfer Capacitance			115		
t _{d(ON)}	Turn-on Delay Time	V _{DD} =20V, I _{DS} =20A, V _{GS} =10V, R _G =3Ω		10		ns
t _r	Turn-on Rise Time			17		
t _{d(OFF)}	Turn-off Delay Time			29		
t _f	Turn-off Fall Time			11		
Gate Charge Characteristics ^⑥						
Q _g	Total Gate Charge	V _{DS} =20V, V _{GS} =10V, I _{DS} =20A		43		nC
Q _{gs}	Gate-Source Charge			6		
Q _{gd}	Gate-Drain Charge			11		

Notes:

- ①Pulse width limited by safe operating area.
- ②Calculated continuous current based on maximum allowable junction temperature. The package limitation current is 50A.
- ③When mounted on 1 inch square copper board, $t \leq 10\text{sec}$.
- ④Limited by T_{Jmax} , $I_{AS} = 12\text{A}$, $L = 0.5\text{mH}$, $V_{DD} = 24\text{V}$, $R_G = 25\Omega$, Starting $T_J = 25^\circ\text{C}$.
- ⑤Pulse test; Pulse width $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$.
- ⑥Guaranteed by design, not subject to production testing.

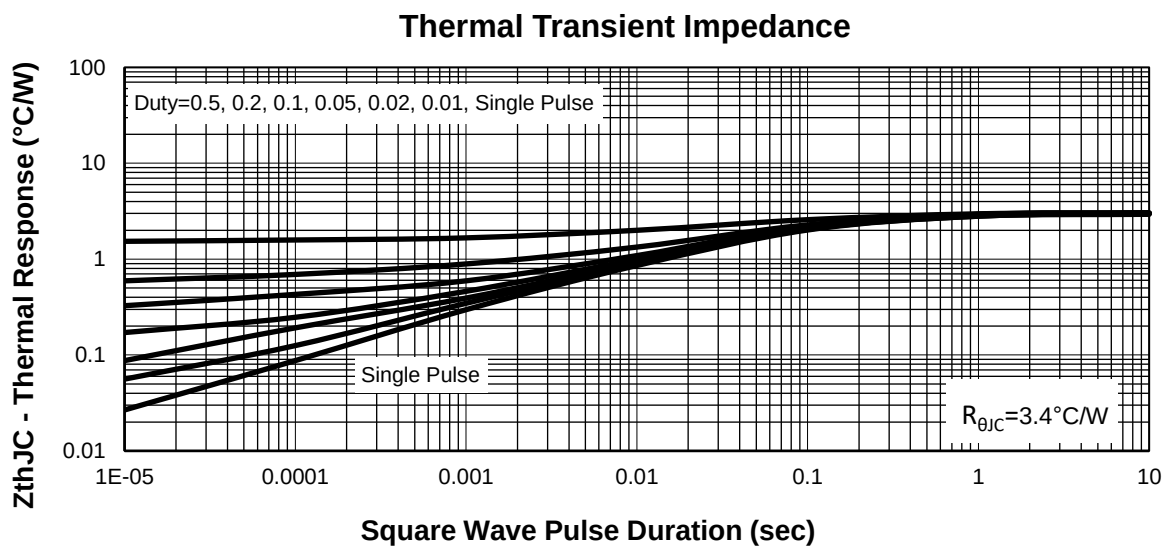
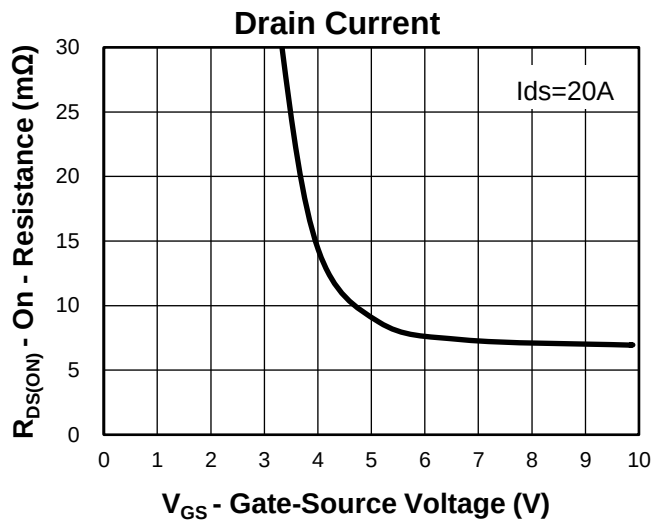
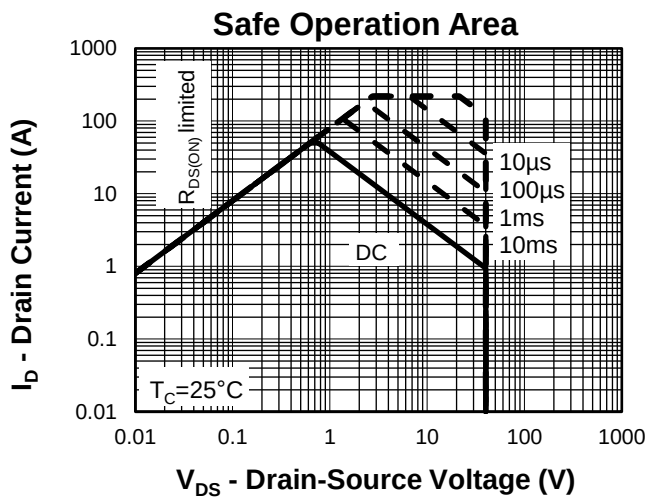
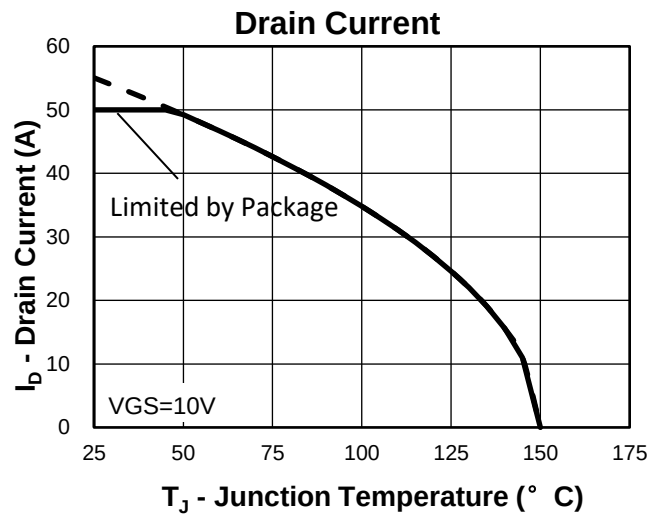
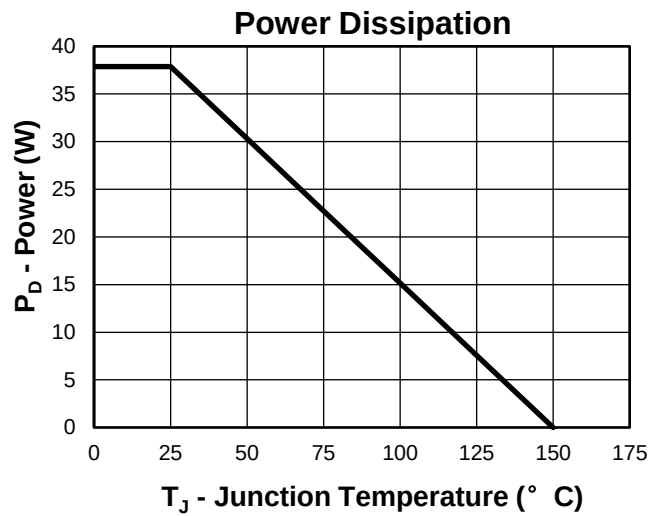
Ordering and Marking Information

Device	Package	Packaging	Quantity	Reel Size	Tape width
KS4210NA	PDFN5060	Tape&Reel	5000	13"	12mm

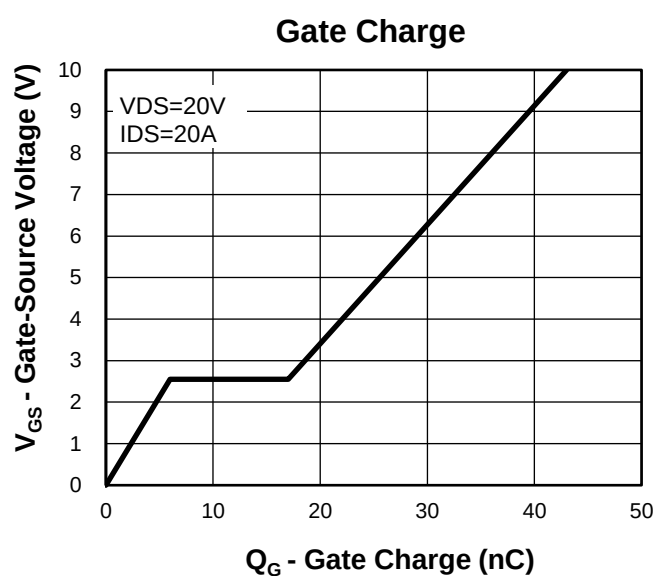
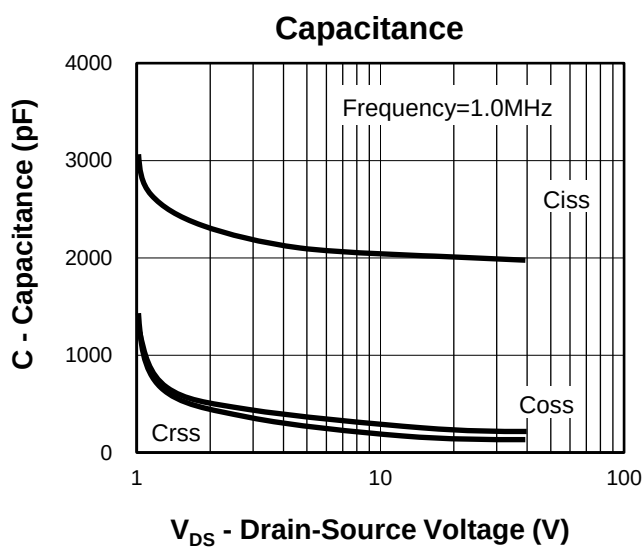
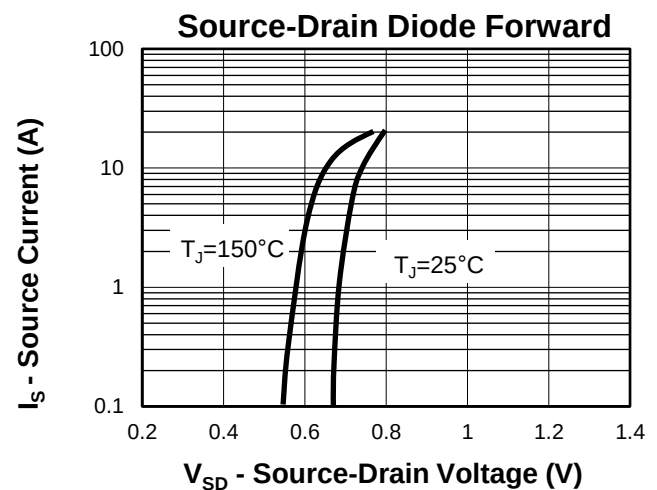
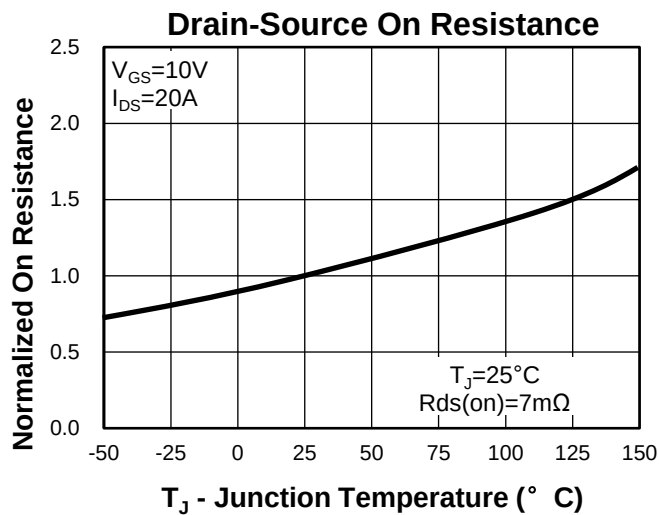
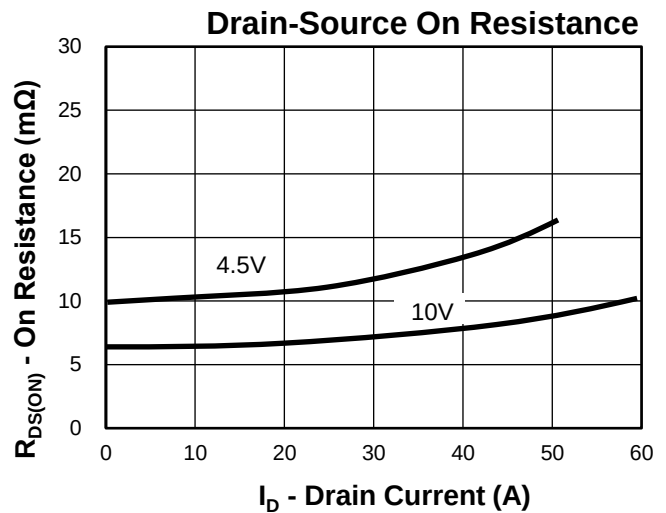
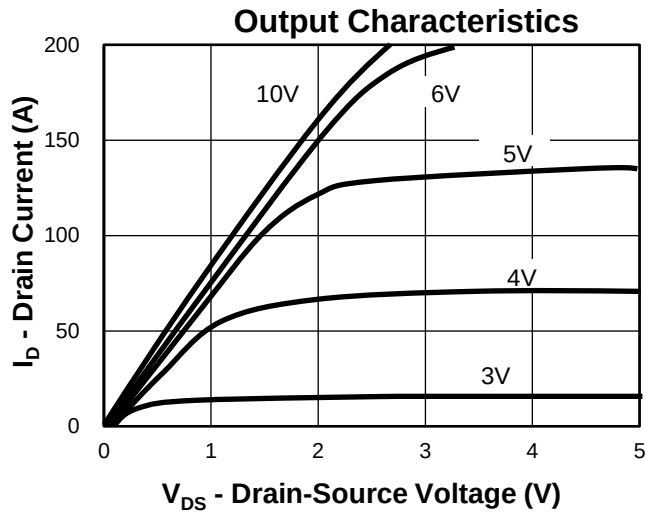


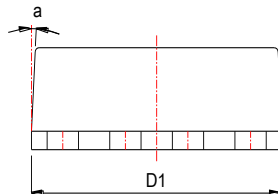
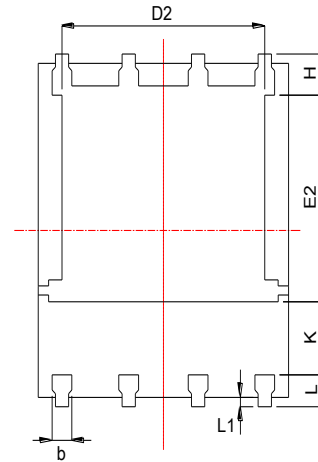
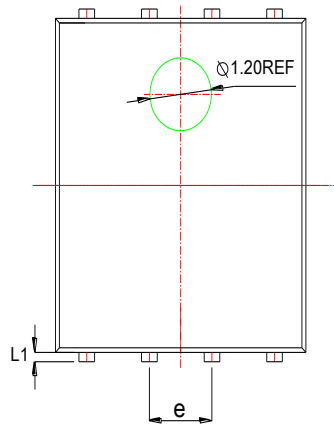
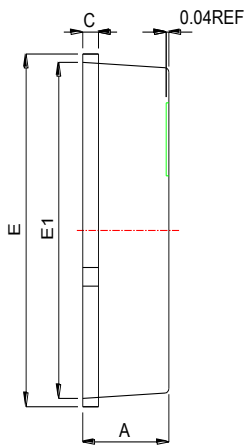
Y =Year,2017-A,2018-B,etc.
 WW =Week.
 XXX =Lot number.

Typical Characteristics

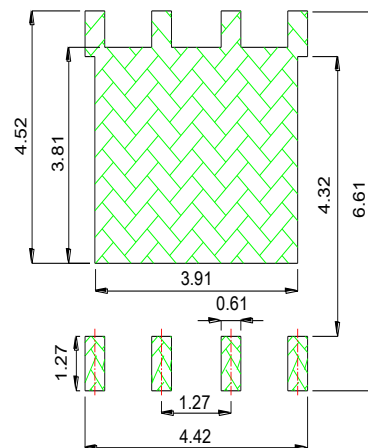


Typical Characteristics



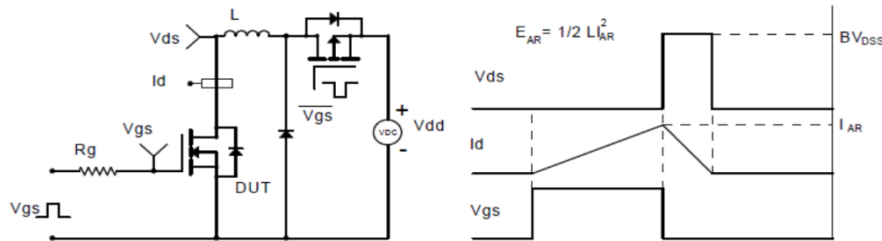
Package Information
PDFN5060


Land Pattern
(Only for Reference)

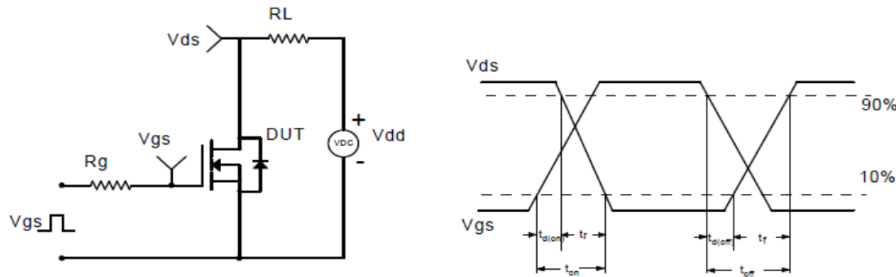


SYMBOL	MM			INCH		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.90	1.00	1.10	0.035	0.039	0.043
b	0.33	0.42	0.51	0.013	0.017	0.020
c	0.20	0.25	0.30	0.008	0.010	0.012
D1	4.80	4.90	5.00	0.189	0.193	0.197
D2	3.61	3.79	3.96	0.142	0.149	0.156
E	5.90	6.00	6.10	0.232	0.236	0.240
E1	5.65	5.75	5.85	0.222	0.226	0.230
E2	3.38	3.58	3.78	0.133	0.141	0.149
e	1.27 BSC			0.050 BSC		
H	0.41	0.51	0.61	0.016	0.020	0.024
k	1.10			0.043		
L	0.51	0.61	0.71	0.020	0.024	0.028
L1	0.06	0.13	0.20	0.002	0.005	0.008
a	0°		12°	0°		12°

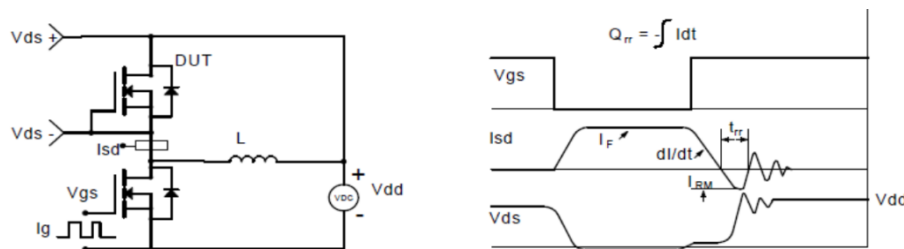
Avalanche Test Circuit and Waveforms



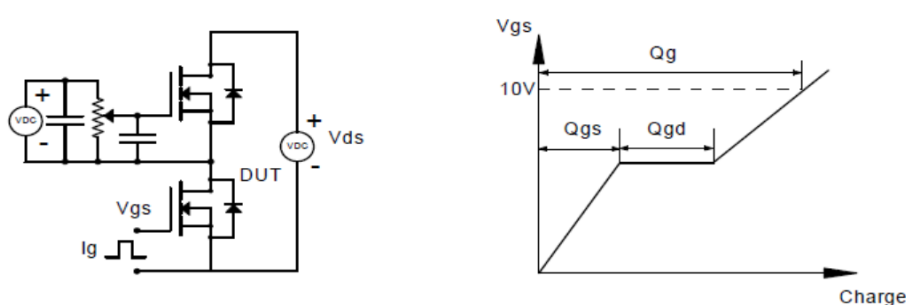
Switching Time Test Circuit and Waveforms



Diode Recovery Test Circuit and Waveforms



Gate Charge Test Circuit and Waveform



Customer Service

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